L Number	Hits	Search Text	DB	Time stamp
-	83	heat near sink with ((bottom adj surface) near5 expos\$3)	USPAT;	2004/09/03 06:45
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
-	6	(heat near sink with ((bottom adj surface) near5 expos\$3)) and	USPAT;	2004/09/03 06:46
		conductive near plate and semiconductor near (chip device)	US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
-	2808	(257/625,675,706,707,796).CCLS.	USPAT;	2004/09/03 06:50
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
-	2264	(438/122,123,125).CCLS.	USPAT;	2004/09/03 06:51
<u> </u>			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
1			IBM_TDB	
-	5	((257/625,675,706,707,796).CCLS.) and first near3 electrode and	USPAT;	2004/09/03 06:54
		second near3 electrode with (smaller bigger)	US-PGPUB;	·
			ЕРО; ЈРО;	
			DERWENT;	
	<u>.</u>	((222)	IBM_TDB	0004/00/00 04 50
-	5	(((257/625,675,706,707,796).CCLS.) and first near3 electrode and	USPAT;	2004/09/03 06:53
		second near3 electrode with (smaller bigger)) not	US-PGPUB;	
		(((438/122,123,125).CCLS.) and first near3 electrode and second near3	EPO; JPO;	
		electrode with (smaller bigger))	DERWENT;	
	_	(//20/100 102 105) OOL 0) 1 5 2 -1 1 1 2	IBM_TDB	2004/00/02 06:54
-	5	((438/122,123,125).CCLS.) and first near3 electrode and second near3	USPAT;	2004/09/03 06:54
		electrode with (smaller bigger)	US-PGPUB;	
1			ЕРО; ЛРО;	
			DERWENT;	
	80	(((semiconductor and heat adj sink) and first near chip) and second near	IBM_TDB USPAT;	2004/09/03 06:57
-	80	(((semiconductor and neat adj sink) and first near chip) and second near chip) and electrode	USPAT, US-PGPUB;	2004/03/03 00:37
		comp) and electrode	EPO; JPO;	
			DERWENT;	
			IBM TDB	
		I	I mini I DB	1